

CMOD4448

**SURFACE MOUNT  
HIGH SPEED  
SILICON SWITCHING DIODE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMOD4448 type is a ultra-high speed silicon switching diode manufactured by the epitaxial planar process, epoxy molded in an ULTRAmimi™ surface mount package, designed for high speed switching applications.

**MARKING CODE: 48**

**ULTRAmimi™**



**SOD-523 CASE**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

**SYMBOL**

$V_R$	75
$V_{RRM}$	100
$I_F$	250
$I_{FRM}$	500
$I_{FSM}$	4.0
$I_{FSM}$	1.0
$P_D$	250
$T_J, T_{stg}$	-65 to +150
$\theta_{JA}$	500

**UNITS**

V
V
mA
mA
A
A
mW
$^\circ\text{C}$
$^\circ\text{C/W}$

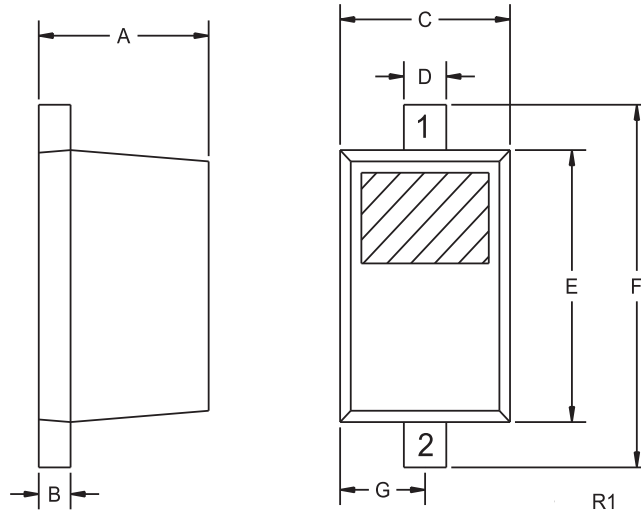
**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_R$	$V_R=20\text{V}$		25	nA
$BV_R$	$I_R=5.0\mu\text{A}$	75		V
$BV_R$	$I_R=100\mu\text{A}$	100		V
$V_F$	$I_F=5.0\text{mA}$	0.62	0.72	V
$V_F$	$I_F=100\text{mA}$		1.0	V
$C_T$	$V_R=0, f=1.0\text{MHz}$		4.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\text{mA}$		4.0	ns

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**SOD-523 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) Cathode
- 2) Anode

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<b>DIMENSIONS</b>				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.020	0.031	0.50	0.80
B	0.004	0.008	0.10	0.20
C	0.028	0.035	0.70	0.90
D	0.008	0.011	0.20	0.28
E	0.039	0.055	1.00	1.40
F	0.055	0.071	1.40	1.80
G	0.016		0.40	

SOD-523 (REV: R1)

R4 (25-January 2010)